

FEATURES

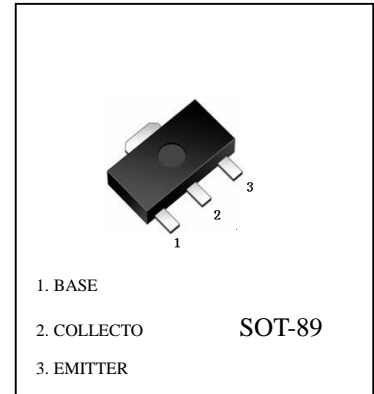
- Very small size making it easy to provide
- High-density, small-size hybrid IC'S

Marking: BB

Maximum Ratings (Ta=25 °C unless otherwise noted)

Parameter	Symbol	Rating	Unit
Collector to base voltage	V _{CBO}	-25	V
Collector to emitter voltage	V _{CEO}	-25	V
Emitter to base voltage	V _{EBO}	-5	V
Collector current	I _C	-1	A
Collector current (pulse) *	I _C	-2	A
Total power dissipation	P _T	0.5	W
Junction temperature	T _j	150	°C
Storage temperature range	T _{stg}	-55 to +150	°C

2SB1119 (PNP)



ELECTRICAL CHARACTERISTICS (@ Ta=25 °C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{CBO}	I _C =-10μA I _E =0	-25			V
Collector-emitter breakdown voltage	V _{CEO}	I _C =-1mA I _B =0	-25			V
Emitter-base breakdown voltage	V _{EBO}	I _E =-10μA I _C =0	-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-20V I _E =0			-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-4V, I _C =0			-0.1	μA
DC current gain	h _{FE}	V _{CE} =-2V I _C =-50mA V _{CE} =-2V I _C =-1A	100 40		560	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-500mA I _B =-50mA		-0.1	-0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-500mA I _B =-50mA		-0.85	-1.2	V
Transition frequency	f _T	V _{CE} =-10V, I _C =-50mA,		180		MHz
Output Capacitance	C _{ob}	V _{CB} =-10V f=1.0MHz I _E =0		15		pF

2SB1119 Typical Characteristics

